Abstracts

A 60GHz - Band Ultra Low Noise Planer - Doped HEMT

T. Katoh, N. Yoshida, H. Minami, T. Kashiwa and S. Orisaka. "A 60GHz - Band Ultra Low Noise Planer - Doped HEMT." 1993 MTT-S International Microwave Symposium Digest 93.1 (1993 Vol. I [MWSYM]): 337-340.

An ultra low noise AlGaAs/InGaAs HEMT with a 0.15µm T-shaped gate and Si planer-doped layer has been developed for millimeter-wave systems. The HEMT showed the extremely reduced minimum noise figure of 1.6dB and high associated gain of 6.5dB at 60GHz. The noise figure is the lowest value ever reported for the AlGaAs/InGaAs pseudomorphic HEMT.

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